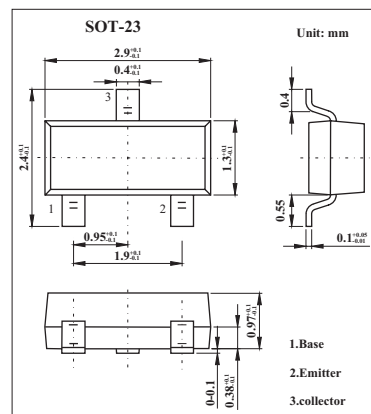


Silicon NPN Epitaxial

2SC2463

■ Features

- Low frequency amplifier.

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	55	V
Collector-emitter voltage	V_{CEO}	50	V
Emitter-base voltage	V_{EBO}	5	V
Collector current	I_C	100	mA
Collector dissipation	P_C	150	mW
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

■ Electrical Characteristics $T_a = 25^\circ\text{C}$

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}$, $I_E = 0$	55			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}$, $R_{BE} = \infty$	50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 10\mu\text{A}$, $I_C = 0$	5			V
Collector cutoff current	I_{CBO}	$V_{CB} = 30\text{V}$, $I_E = 0$			0.5	μA
Emitter cutoff current	I_{EBO}	$V_{EB} = 2\text{V}$, $I_C = 0$			0.5	μA
DC current gain	h_{FE}	$V_{CE} = 12\text{V}$, $I_C = 2\text{mA}$	250		1200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{mA}$, $I_B = 1\text{mA}$			0.5	V
Base-emitter voltage	V_{BE}	$V_{CE} = 12\text{V}$, $I_C = 2\text{mA}$			0.75	V

■ h_{FE} Classification

Marking	DD	DE	DF
h_{FE}	250~500	400~800	600~1200